IN THE CLIAMS:

Please add new claims 21-28 as follows:

- 1. (Original) A method for depositing a low dielectric constant film on a substrate, comprising reacting two or more organosiloxanes selected from the group of consisting 1,3-dimethyldisiloxane, 1,1,3,3-tetramethyldisiloxane. hexamethyldisiloxane, 1,3-bis(silanomethylene)disiloxane, bis(1methyldisiloxanyl)methane, 2,2-bis(1-methyldisiloxanyl)propane, 1,3,5,7tetramethylcyclotetrasiloxane, octamethylcyclotetrasiloxane, 1.3.5.7.9pentamethylcyclopentasiloxane, 1,3,5,7-tetrasilano-2,6-dioxy-4,8-dimethylene, 1,3,5trisilanetetrahydropyran, and 2,5-disilanetetrahydrofuran while applying RF power, wherein the low dielectric constant film comprises silicon-carbon bonds and a dielectric constant of about 3 or less.
- 2. (Original) The method of claim 1, wherein at least one of the organosiloxanes is cyclic and comprises C, H, and O.
- 3. (Original) The method of claim 2, wherein the cyclic organosiloxane comprising C, H, and O is 1,3,5,7-tetramethylcyclotetrasiloxane.
- 4. (Original) The method of claim 1, wherein the two or more organosiloxanes are reacted with an oxidizing gas.
- 5. (Original) The method of claim 4, wherein the oxidizing gas is selected from the group consisting of oxygen, ozone, nitrous oxide, carbon dioxide, and water.
- 6. (Original) The method of claim 1, wherein the RF power is pulsed to increase the porosity of the film.
- 7. (Original) A method for depositing a low dielectric constant film on a

substrate, comprising reacting two or more organosiloxanes selected from the group consisting of 1,3,5,7-tetramethylcyclotetrasiloxane, octamethylcyclotetrasiloxane, 1,3,5,7,9-pentamethylcyclopentasiloxane, 1,3,5,7-tetrasilano-2,6-dioxy-4,8-dimethylene, 1,3,5-trisilanetetrahydropyran, and 2,5-disilanetetrahydrofuran while applying RF power, wherein the low dielectric constant film comprises silicon-carbon bonds and a dielectric constant of about 3 or less.

- 8. (Original) The method of claim 7, wherein at least one of the organosiloxanes is selected from the group consisting of 1,3,5-trisilanetetrahydropyran, and 2,5-disilanetetrahydrofuran.
- 9. (Original) The method of claim 7, wherein the two or more organosiloxanes are reacted with an oxidizing gas while applying RF power.
- 10. (Original) The method of claim 9, wherein the oxidizing gas is selected from the group consisting of oxygen, ozone, nitrous oxide, carbon dioxide, and water.
- 11. (Original) The method of claim 7, wherein the RF power is pulsed to increase the porosity of the film.
- 12. A method for depositing a low dielectric constant film on a (Original) substrate, comprising reacting two or more organosilanes selected from the group dimethylsilane, trimethylsilane, dimethylsilanediol, consisting of methylsilane, phenylsilane, diphenylsilane, diphenylsilanediol, methylphenylsilane, ethylsilane, bis(methylsilano)methane, 1,2-disilanoethane, 1,2disilanomethane. bis(methylsilano)ethane, 2,2-disilanopropane, and 1,3,5-trisilano-2,4,6-trimethylene, while applying RF power, wherein the low dielectric constant film comprises siliconcarbon bonds and a dielectric constant of about 3 or less.
- 13. (Original) The method of claim 12, wherein one of the organosilanes is 1,3,5-trisilano-2,4,6-trimethylene.

- 14. (Original) The method of claim 12, wherein the two or more organosilanes are reacted with an oxidizing gas.
- 15. (Original) The method of claim 14, wherein the oxidizing gas is selected from the group consisting of oxygen, ozone, nitrous oxide, carbon dioxide, and water.
- 16. (Original) The method of claim 12, wherein the RF power is pulsed to increase the porosity of the film.
- 17. (Original) A method for depositing a low dielectric constant film on a substrate, comprising reacting two or more organosiloxanes, wherein a first organosiloxane of the two or more organosiloxanes is cyclic and comprises C, H, and O and a ring comprising carbon and oxygen, and a second organosiloxane of the two or more organosiloxanes is selected from the group consisting 1,3,5,7tetramethylcyclotetrasiloxane, octamethylcyclotetrasiloxane, 1,3,5,7,9and pentamethylcyclopentasiloxane, while applying RF power, wherein the low dielectric constant film comprises silicon-carbon bonds and a dielectric constant of about 3 or less.
- 18. (Original) The method of claim 17, wherein the first organosiloxane is selected from the group consisting of 1,3,5-trisilanetetrahydropyran, 2,5-disilanetetrahydrofuran, and 1,3,5,7-tetrasilano-2,6-dioxy-4,8-dimethylene.
- 19. (Original) The method of claim 18, wherein the first organosiloxane is 1,3,5,7-tetrasilano-2,6-dioxy-4,8-dimethylene.
- 20. (Original) The method of claim 17, wherein the two or more organosiloxanes are reacted with an oxidizing gas.

21. (New) A method for depositing a low dielectric constant film on a substrate, comprising plasma assisted reaction of a mixture comprising an oxidizing gas and a siloxane comprising

wherein the low dielectric constant film comprises silicon-carbon bonds and a dielectric constant of about 3 or less.

- 22. (New) The method of claim 21, wherein the mixture further comprises a siloxane selected from the group consisting of 1,3-dimethyldisiloxane, 1,1,3,3-tetramethyldisiloxane, 1,3,5,7-tetramethylcyclotetrasiloxane, octamethylcyclotetrasiloxane, bis(1-methyldisiloxanyl)-methane, 2,2-bis(1-methyldisiloxanyl)propane, and 2,5-disilanetetrahydrofuran.
- 23. (New) The method of claim 21, wherein the siloxane is selected from the group consisting of 1,3-bis(silanomethylene)disiloxane, 1,3,5,7-tetrasilano-2,6-dioxy-4,8-dimethylene, and 1,3,5-trisilanetetrahydropyran.
- 24. (New) The method of claim 21, wherein the siloxane is 1,3-bis(silanomethylene)disiloxane.
- 25. (New) The method of claim 24, wherein the oxidizing gas is N₂O.
- 26. (New) The method of claim 21, wherein the mixture further comprises an inert gas.
- 27. (New) The method of claim 21, wherein the plasma is formed by RF power comprising high frequency RF power.
- 28. (New) The method of claim 27, wherein the high frequency RF power is pulsed.